



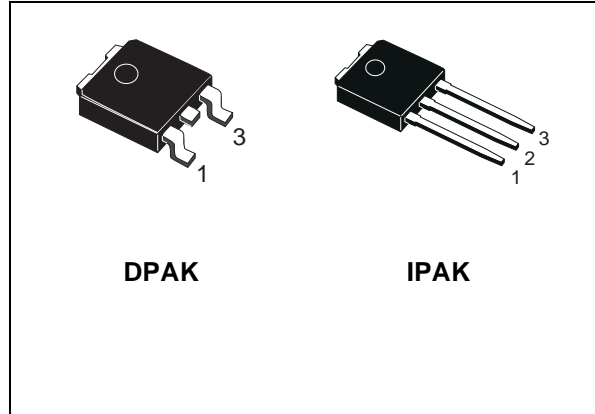
# STD30PF03L STD30PF03L-1

P-CHANNEL 30V - 0.025Ω - 24A DPAK/IPAK  
STripFET™ II POWER MOSFET

PRELIMINARY DATA

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STD30PF03L	30 V	< 0.028Ω	24 A
STD30PF03L-1	30 V	< 0.028Ω	24 A

- TYPICAL R<sub>DS(on)</sub> = 0.025Ω
- STANDARD OUTLINE FOR EASY AUTOMATED SURFACE MOUNT ASSEMBLY
- LOW THRESHOLD DRIVE
- LOW GATE CHARGE
- EXTREMELY LOW FIGURE OF MERIT (R<sub>DS(on)</sub> \* Q<sub>g</sub>)

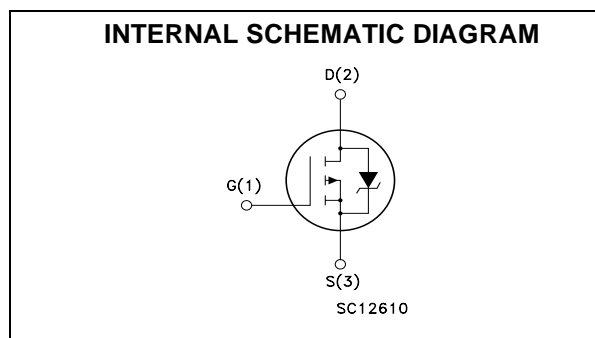


## DESCRIPTION

This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance and low gate charge.

## APPLICATIONS

- DC-DC CONVERTERS



## ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	30	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	30	V
V <sub>GS</sub>	Gate- source Voltage	± 16	V
I <sub>D</sub> (#)	Drain Current (continuous) at T <sub>C</sub> = 25°C	24	A
I <sub>D</sub> (#)	Drain Current (continuous) at T <sub>C</sub> = 100°C	24	A
I <sub>DM</sub> (●)	Drain Current (pulsed)	96	A
P <sub>TOT</sub>	Total Dissipation at T <sub>C</sub> = 25°C	70	W
	Derating Factor	0.47	W/°C
T <sub>stg</sub>	Storage Temperature	- 55 to 175	°C
T <sub>j</sub>	Max. Operating Junction Temperature	175	°C

(●) Pulse width limited by safe operating area  
(#) Current limited by wire bonding

Note: For the P-CHANNEL MOSFET actual polarity of voltages and current has to be reversed

## STD30PF03L - STD30PF03L-1

### THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	2.14	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	100	°C/W
T <sub>j</sub>	Maximum Operating Junction Temperature	275	°C

### AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max)	24	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 25 V)	350	mJ

### ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0	30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating, T <sub>C</sub> = 125 °C			1 10	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 16 V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	1			V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 12 A V <sub>GS</sub> = 5 V, I <sub>D</sub> = 12 A		0025 0.032	0.028 0.040	Ω Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (1)	Forward Transconductance	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 12 A		23		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V, f = 1 MHz, V <sub>GS</sub> = 0		1670		pF
C <sub>oss</sub>	Output Capacitance			345		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			120		pF

**ELECTRICAL CHARACTERISTICS (CONTINUED)**

**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 24\text{ V}$ , $I_D = 24\text{ A}$ $R_G = 4.7\Omega$ , $V_{GS} = 4.5\text{V}$ (see test circuit, Figure 3)		64		ns
$t_r$	Rise Time			122		ns
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 15\text{ V}$ , $I_D = 24\text{ A}$ , $V_{GS} = 5\text{ V}$		18.5 5.5 11	25	nC nC nC

**SWITCHING OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ $t_f$	Turn-off-Delay Time Fall Time	$V_{DD} = 24\text{ V}$ , $I_D = 24\text{ A}$ , $R_G = 4.7\Omega$ , $V_{GS} = 4.5\text{V}$ (see test circuit, Figure 3)		36 26		ns ns

**SOURCE DRAIN DIODE**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				24	A
$I_{SDM(2)}$	Source-drain Current (pulsed)				96	A
$V_{SD(1)}$	Forward On Voltage	$I_{SD} = 24\text{ A}$ , $V_{GS} = 0$			2.3	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 24\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 24\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$ (see test circuit, Figure 5)		40 52 2.6		ns $\mu\text{C}$ A

Note: 1. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.  
2. Pulse width limited by safe operating area.

Fig. 1: Unclamped Inductive Load Test Circuit

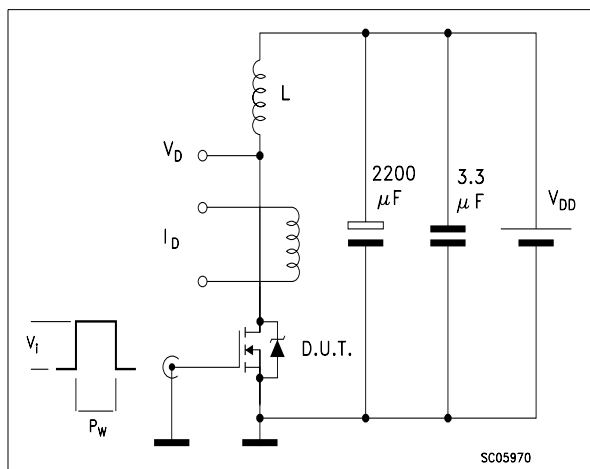


Fig. 2: Unclamped Inductive Waveform

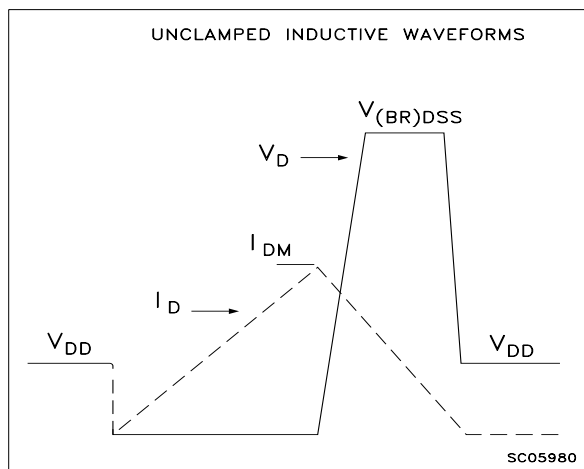


Fig. 3: Switching Times Test Circuit For Resistive Load

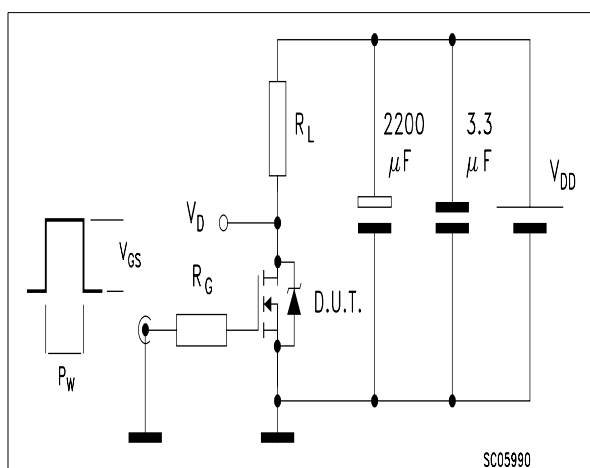


Fig. 4: Gate Charge test Circuit

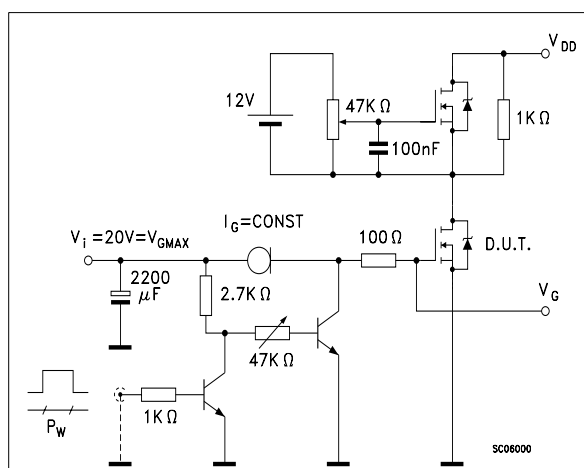
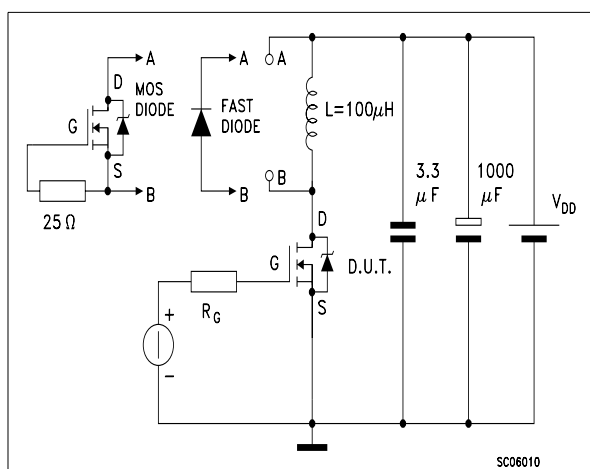
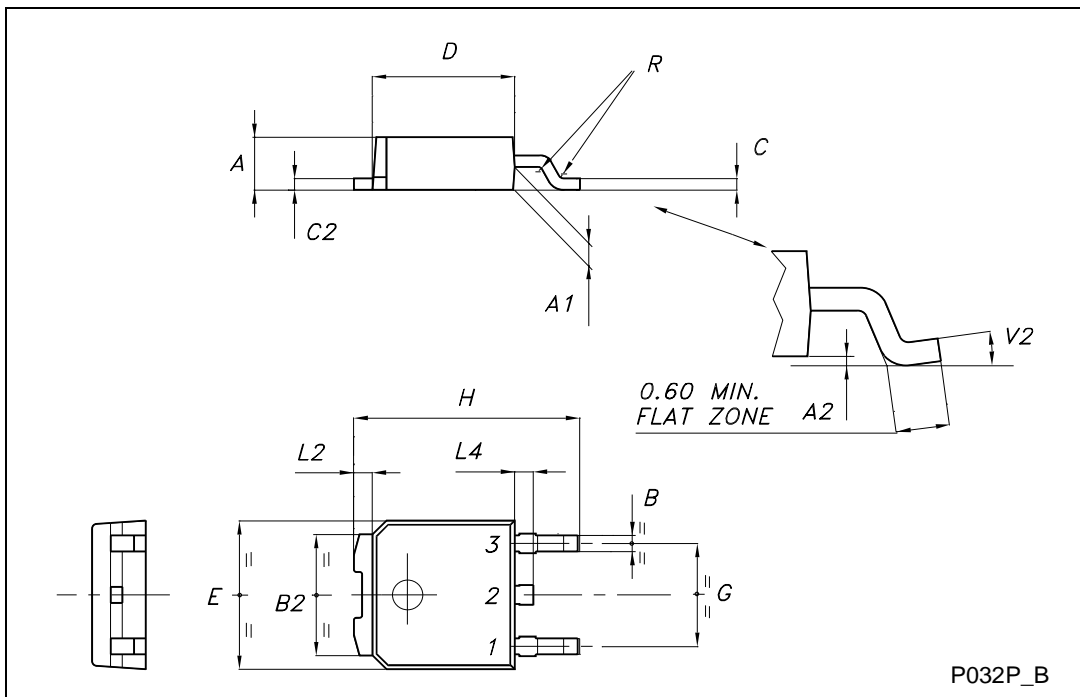


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



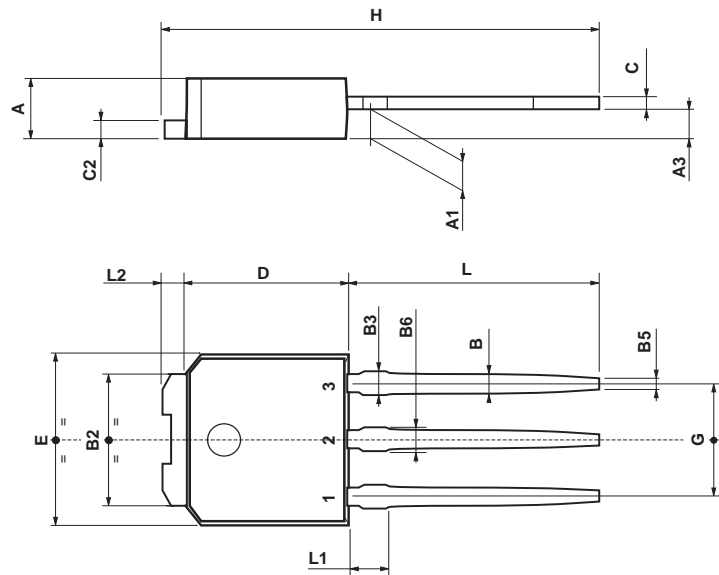
TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
C	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°



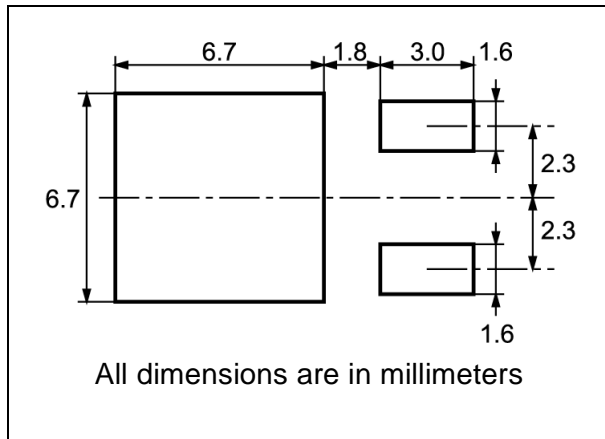
TO-251 (IPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.031
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.012	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039

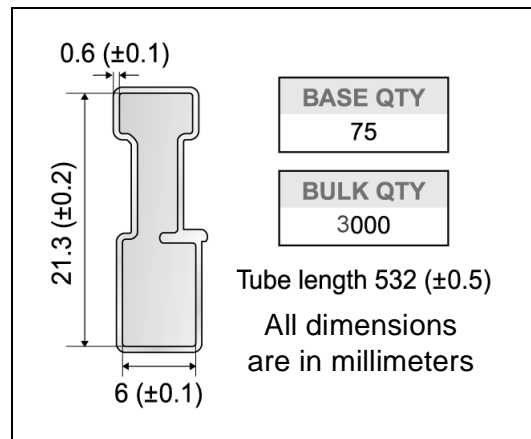


0068771-E

**DPAK FOOTPRINT**



**TUBE SHIPMENT (no suffix)\***



**TAPE AND REEL SHIPMENT (suffix "T4")\***

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

G measured at hub

**REEL MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

BASE QTY	BULK QTY
2500	2500

**TAPE MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641

TOP COVER TAPE

10 pitches cumulative tolerance on tape +/- 0.2 mm

Center line of cavity

User Direction of Feed

For machine ref. only including draft and radii concentric around B0

FEED DIRECTION

Bending radius R min.

\* on sales type



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